Electronic Supplementary Material (ESI) for Journal of Materials Chemistry C.

Supporting Information for

Low turn-on voltage and highly bright Ag-In-Zn-S quantum dot light-emitting diodes

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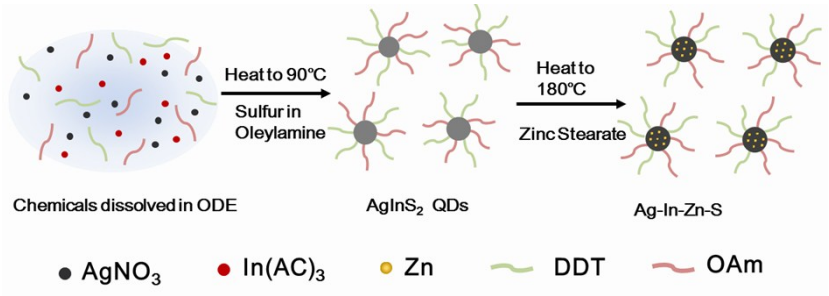

Scheme S1 The schematic illustration of the synthetic process of Ag-In-Zn-S QDs.

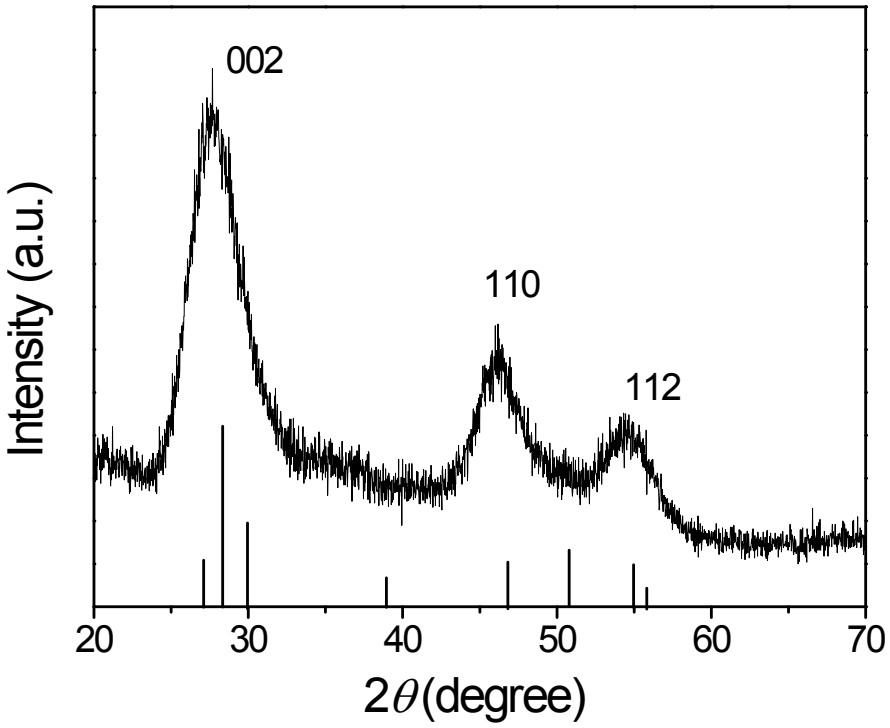

Figure S1 The XRD pattern of Ag-In-Zn-S QDs.

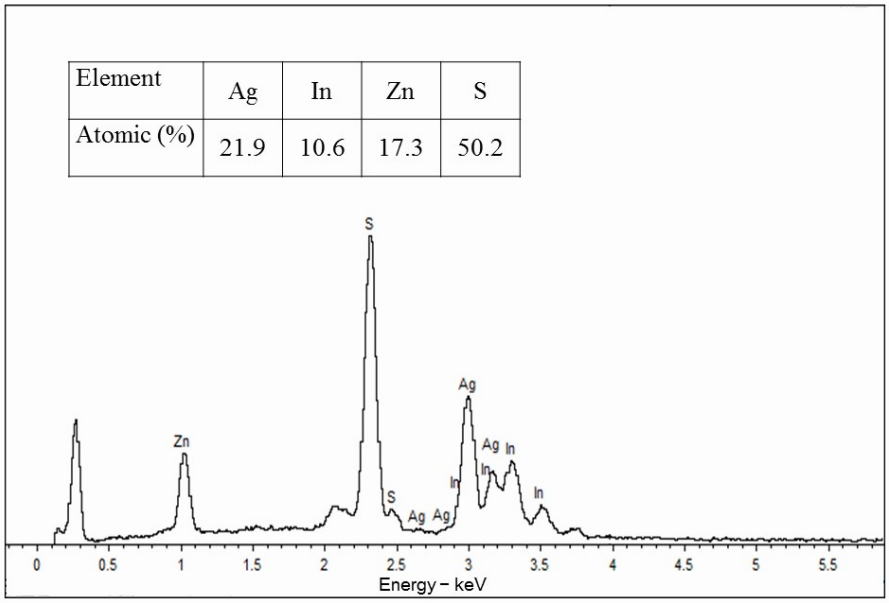

Figure S2 EDS data of the corresponding Ag-In-Zn-S QDs.

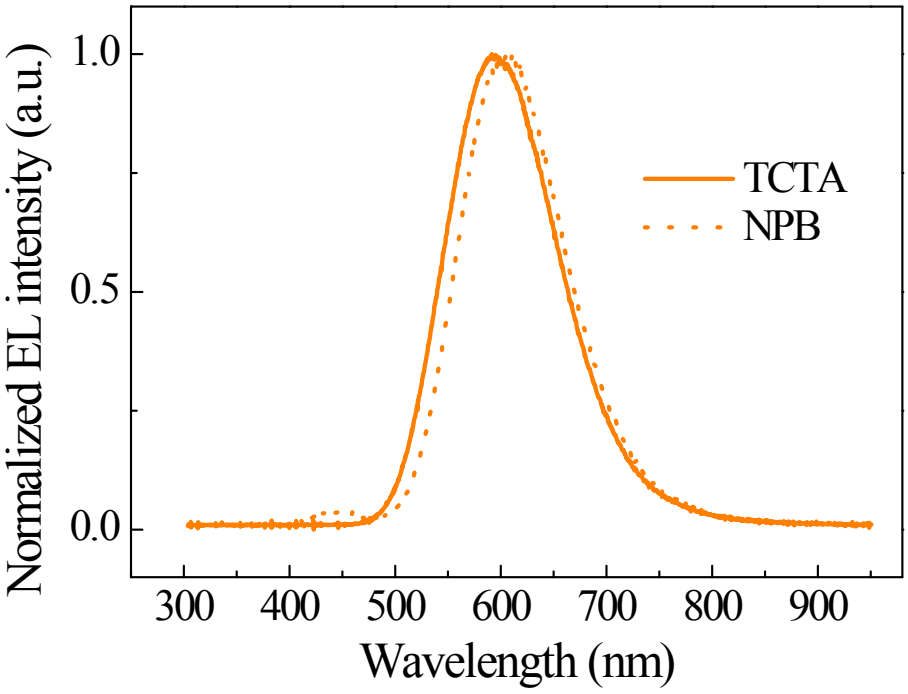

Figure S3 Normalized EL spectra of devices A and D based on TCTA and NPB, respectively. The devices were driven at voltage of 4.5 V.

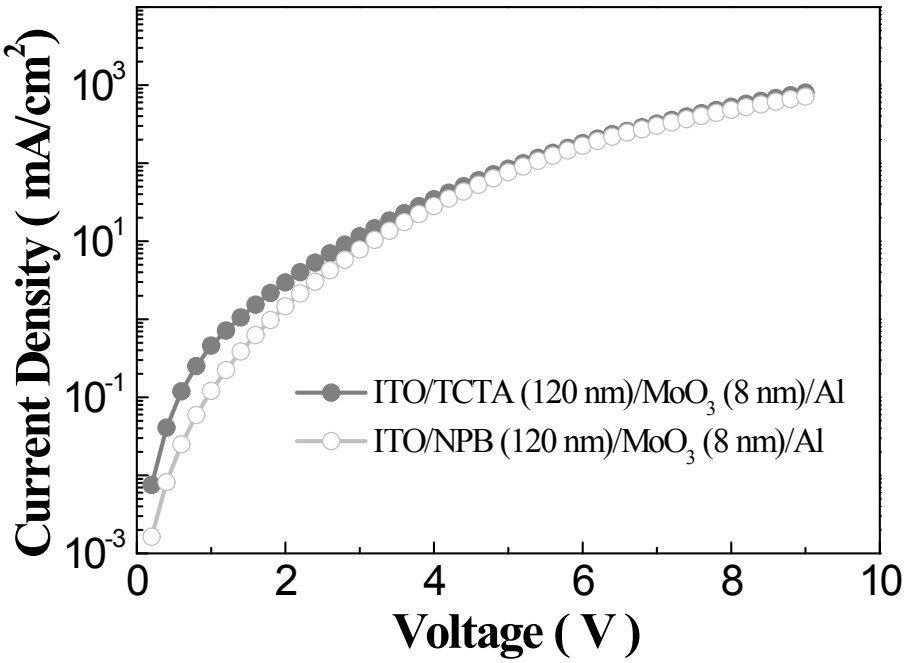

Figure S**4**. Voltage-current density properties of hole-only devices based on different HTLs, the thicknesses of TCTA and NPB were 120 nm to avoid the electrical shortcuts due to the formation of island structure on ITO surface. Al is used as the anode.